



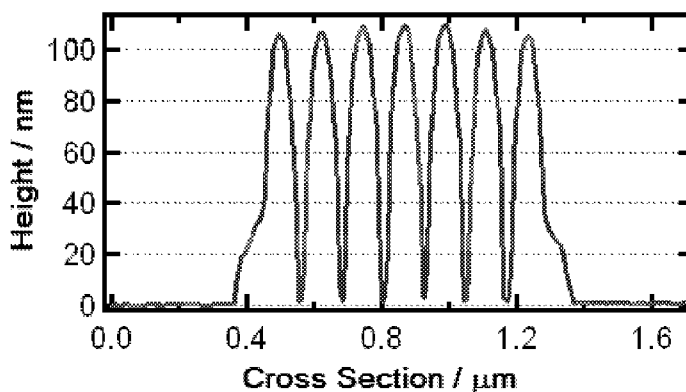
- (51) **International Patent Classification:**
G03F 7/32 (2006.01) *C11D 1/40* (2006.01)
- (21) **International Application Number:**
PCT/IB2013/055392
- (22) **International Filing Date:**
1 July 2013 (01.07.2013)
- (25) **Filing Language:** English
- (26) **Publication Language:** English
- (30) **Priority Data:**
61/669686 10 July 2012 (10.07.2012) US
- (71) **Applicant:** BASF SE [DE/DE]; 67056 Ludwigshafen (DE).
- (71) **Applicant (for MN only):** BASF (CHINA) COMPANY LIMITED [CN/CN]; 300 Jiangxinsha Road, Shanghai, 200137 (CN).
- (71) **Applicant (for AL, AT, BA, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR only):** BASF SCHWEIZ AG [CH/CH]; Klybeckstrasse 141, CH-4057 Basel (CH).
- (72) **Inventors:** KLIPP, Andreas; Viktoriarig 15, 67245 Lambsheim (DE). HONCIUC, Andrei; Schmale Gasse 1, 67063 Ludwigshafen (DE). OETTER, Günter; Hans-von-Marees-Str.21, 67227 Frankenthal (DE). BITTNER, Christian; Niederwaldstr. 50, 64625 Bensheim (DE).
- (74) **Common Representative:** BASF SE; 67056 Ludwigshafen (DE).
- (81) **Designated States** (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.
- (84) **Designated States** (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

Published:

- with international search report (Art. 21(3))
- before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments (Rule 48.2(h))

(54) **Title:** COMPOSITIONS FOR ANTI PATTERN COLLAPSE TREATMENT COMPRISING GEMINI ADDITIVES

Fig. 2



(57) **Abstract:** The use of a Gemini additive in compositions for treating semiconductor substrates is provided. The compositions are useful in processes for manufacturing integrated circuits devices, optical devices, micromachines and mechanical precision devices, in particular for developing photoresists and post etch residue removal to avoid pattern collapse.